

## Index

- $\alpha_T$ , *see* base transport factor
- $\beta_F$  (current gain), *see* BJT
- $\gamma$ , *see* margin angle
- $\gamma_E$ , *see* emitter efficiency
- $\omega_s$ -component, 314, *see* control
- $\psi_o$ , 470
- $\tau_a$ , *see* ambipolar lifetime
- ac/ac converter, 12, 20–22, 289
  - ac controller, 21
  - solid-state transformer, 290
  - with dc link, 21, 289
    - energy storage in, 290
    - with dc-link, 22
      - sizing bus capacitor, 293
  - See also* cycloconverter
- ac/dc converter, 13–18
  - control of, 425–428
  - filter, 16
    - See also* rectifier
- active resonant-commutated pole, *see* ARCP
- $A_{CW_A}$  (core area product), *see* inductor
- Alcator-C, 578
- ambipolar diffusion constant, 501
- ambipolar diffusion length, 501
- ambipolar lifetime, 500
- Ampère's law, 547
- ampere-turns, 550
- angle of retard, *see* SCR
- apparent power, 38, 624
  - See also* power factor
- ARCP, 746
- ASCR, *see* SCR
- assumed states, 30
- audio susceptibility, 349
- average value analysis, 81
- averaged circuit, *see* control
- averaging
  - generalized circuit, 354
- base drive, 693–695, 704
  - See also* BJT
- battery charger, 110
- beat frequency, 352
- BIBO, *see* control
- bipolar junction transistor, *see* BJT
- BJT, 2, 4, 478–482, 511–516
  - $v$  region, 511
  - base current, 480
  - base drive, 704–716
    - anti-saturation clamp, 716
    - pedestal and porch, 714
    - storage delay time, 715
    - turn-off requirements, 715
    - turn-on requirement, 714
  - base transport factor, 481
  - collector-base breakdown voltage, 442
  - current gain, 442
    - calculation of, 481
    - common-base ( $\alpha_F$ ), 480
    - common-emitter ( $\beta_F$ ), 480, 515
    - common-emitter ( $h_{FE}$ ), 442
  - cut-off, 512
  - Darlington connection, 443
  - drift region, 511
  - emitter defect, 480
  - emitter efficiency, 481, 515
  - high-level injection, 511
  - operating regions, 511
    - forward active, 513
    - hard-saturation, 515
    - quasi-saturation, 514
    - saturation, 482
  - parameters, 480
  - physical model, 478
  - punch-through, 511
  - recombination defect, 480
  - reverse injection, 480
  - safe operating area, 486, 487, 724
  - second breakdown, 487
  - sustaining voltage, 513
  - switching dynamics, 515
  - terminal currents, 478
  - $v-i$  characteristics, 442
- Bode plot, 338, 407–413
- Boltzmann's constant, 463
- boost converter, 84, 106
  - conversion ratio, 88
  - switch implementation, 86
    - with ZVS, 744–746
- bootstrap circuit, 710
- bridge circuit, 14
- buck converter, 84
  - as part of dc/ac bridge, 194
  - as power amplifier, 180
  - element values, 99
  - EMI input filter, 779–780
  - EMI measurements, 772
  - linearizing, 331
  - switch implementation, 84–86
  - with bilateral power, 87
  - with ZVS, 741–742
- buck/boost converter, 90, 91
  - as dc/ac converter, 196
  - averaged circuit for, 326, 348
- control, 420–422
  - compensator design, 410–414, 416–420
  - current-mode, 369
  - feedback, 320, 381
  - feedforward, 317
  - frequency response, 403
  - in continuous conduction, 380
  - open-loop, 317
  - stability, 381, 401
- discontinuous conduction, 326, 332
- element values, 102
- linearized averaged model, 384, 388–390
- non-inverting, 94, 95
  - See also* SEPIC converter
- sampled-data model, 367
- state-space model, 362–364
  - generalized, 369
- step response, 349

**794      Index**

- canonical cell, 82, 89, 92
- capacitor, 452–455
  - as clamp, 139
  - ceramic, 454–455
    - age-dependent permittivity, 454
  - Class II codes, 454
  - classes, 454
  - structure, 454
  - use at high frequencies, 455
  - voltage-dependent permittivity, 454
- dielectric parameters, 452
- dissipation factor, 452
- electric double-layer (DLC), 454
- electrolytic, 453
  - aluminum, 453, 777
  - tantalum, 453
- film
  - construction, 452
  - dielectric material, 452
  - metalized, 452
  - parasitic inductance, 453
  - polycarbonate, 452
  - polypropylene, 452
  - losses in, 439
  - metal-foil, 452
  - x- and y-type, 787
- cat whisker, 437
- characteristic polynomial, 337, 387
  - roots, 337
- charge multipliers, *see*
  - switched-capacitor converter
- chopper, *see* dc/dc converter
- circuit commutated turn-off time, *see*
  - SCR
- circuit replacement by equivalent source, 33, 79
- clamp circuit, 697, 698, 738–739
- clamped inductive load, 446, 538
- Clarke transform, 231–234
  - power invariance, 232
- Clarke, Edith, 232
- Cockcroft–Walton voltage multiplier, 131
- coercive force, 555
- common mode, 783
  - (*see also* EMI)
- common-mode
  - choke, 785
  - transient immunity, 710
- conductivity, 466
  - calculation of, 467
- conductivity modulation, 494
  - (*See also* high-level injection)
- control
  - $\omega_s$ -component, 314
    - averaging to, 350–354
    - local, 350
    - model for RLC circuit, 364
    - state-space model for, 364
  - bandwidth, 329
  - BIBO stability, 393
  - circuit averaging, 324–327
    - KVL and KCL, 324
    - LTI component, 324
    - of buck/boost converter, 326
    - of controlled rectifier, 325
    - switching function, 327
  - compensator design, 410–414, 416–420
    - constant frequency, 84
    - current-mode, 329, 369, 397, 415–420
    - digital, 425–428
      - of ac/dc preregulator, 425–428
    - duty-ratio, 397
    - dynamic behavior, 314–322
      - feedback, 318–322, 332–342, 381, 422–425
      - classical, 333
      - design, 405–413
      - nonlinear state, 423–425
      - pole placement, 423
    - feedforward, 316–318, 321, 329
    - frequency response, 393, 402–405
    - linearizing a circuit, 331–332
    - local  $\omega_s$ -component, 316
    - local average, 315
    - loop gain, 338–340, 409
    - loop transfer function, 335, 339
    - MIMO, 393
    - models
      - $\omega_s$ -averaged circuit, 351
      - averaged-circuit, 323–329, 346–350
        - averaging a switch, 347–350
      - continuous-time LTI, 385–394
      - continuous-time state-space, 354–365
        - delay elements, 367
        - discrete-time, 399–405
        - dynamic, 322–323
        - for  $\omega_s$ -component, 353
        - for controller, 372
        - for interconnected system, 372
        - generalized state-space, 368–372
        - linearization, 330
        - linearized, 329–332
          - linearizing, 378–382, 385, 395–398
      - phase-controlled, *see*
        - phase-controlled converter
      - resonant, *see* resonant converter
    - LTI, 323
    - periodically varying, 357
    - piecewise LTI, 362, 394–395
    - sampled-data, 327, 365–368, 403
    - small-signal, 378
    - state-space, 323, 346, 359, 361–365
      - multi-loop, 414–422
        - design, 414
          - of buck/boost converter, 420–422
        - nonlinearities, 342
        - of dc machine, 414
        - open-loop, 316–318
        - phase crossover frequency, 341
        - phase margin, 341
        - PI controller, 320
        - PID controller, 320
        - robustness, 336, 340–342
        - sensitivity function, 335
        - stability, 330, 336, 381, 401–402
          - asymptotic, 400
        - state-space averaging, 363
      - transfer function
        - of plant, 334
        - system, 336
        - unity-gain crossover frequency, 338
      - controlled rectifier, 57
        - averaged-circuit model for, 325
        - feedback control of, 334
        - loop transfer function, 339
          - See also* phase-controlled converter
      - converter
        - ac/ac, *see* ac/ac converter
        - ac/dc, *see* ac/dc converter
        - boost, *see* boost converter
        - buck, *see* buck converter
        - buck/boost, *see* buck/boost converter
        - Ćuk, *see* Ćuk converter
        - DAB, *see* dual active-bridge
        - dc/ac, *see* dc/ac converter
          - See also* rectifier, inverter
        - dc/dc, *see* dc/dc converter
        - direct, *see* direct converter
        - dual active-bridge, *see* DAB
          - converter, 150
          - as SST, 303
        - flyback, *see* flyback converter
        - flyforward, *see* flyforward converter
        - forward, *see* forward converter
        - indirect, *see* indirect converter
        - matrix, *see* matrix converter
        - phase-controlled, *see*
          - phase-controlled converter
        - resonant, *see* resonant converter

- SEPIC, *see* SEPIC converter
- switched-capacitor, *see*
  - switched-capacitor converter
  - transformer-isolated, 192–194
  - up/down, *see* buck/boost converter
  - variable-frequency, 167
- Zeta, *see* Zeta converter
- core factor, *see* inductor
- core loss, 561–684
  - data, 565
  - eddy current, 561, 675–678
  - ferrous alloys, 561
  - hysteresis, 562, 678–679
  - laminations, 561
  - Steinmetz equation, 562, 679
    - improved, 680
  - with non-sinusoidal flux, 680–684
- core volume  $\mathcal{V}_c$ , 554
- crossover distortion, 181
  - reduction of, 181
- Ćuk converter, 92, 94, 154
  - element values, 102
  - switch stress, 103
- Curie temperature  $T_C$ , 575
- current commutation, 35
- current-source inverter
  - source inductor, 171
- cycloconverter, 20, 21, 289
  - high-frequency-link, 299
  - naturally commutated, 294–297
  - switch implementation, 300
  - with polyphase output, 297
- $D_a$ , *see* ambipolar diffusion constant
- damped natural frequency, 349
- damping factor, 352
- datasheet, 538
- dc machine
  - speed control of, 414
- dc/ac converter, 167–201
  - as power amplifier, 181
  - control of, 168
  - harmonic cancellation, 177–179
  - harmonic elimination, 175–177
  - harmonic reduction, 172–175
    - See also* waveform properties
  - high-frequency bridge, 182
  - inverter current control, 187–189
  - multi-level, 190–192
    - using flying capacitor, 190–192
  - notched waveforms, 175–177
  - power balance between ports, 196
  - pulse-width modulated, 179–187
- pulse-width modulation
  - generating  $d(t)$ , 184
  - THD calculation, 183
  - unfolding bridge, 180
  - waveshaping, 180
- stepped waveform, 179
  - compared to notched, 179
- using buck/boost converters, 196
- variable-frequency
  - bridge, 167
  - with ac-voltage-source load, 170
    - control of, 170
- dc/dc converter, 12, 18–20
  - discontinuous conduction, 106–108
  - filter element values, 95
- isolated, 136–158
  - active clamp, 143
  - clamp energy recovery, 139
  - clamp voltage, 139
  - control of, 146
  - core resetting, 138
  - Ćuk converter, 154
  - double-ended, 145–150, 152
  - dual active-bridge, 150
  - flyback, 136, 153–154
  - flyforward, 141
  - forward, 136
  - hybrid bridge, 141
  - leakage inductance effects, 155–157
  - magnetizing current, 138
  - push–pull, 150
  - SEPIC, 154
  - transformer-coupled clamp, 140
  - voltage clamping, 138
  - with multiple outputs, 158
  - Zeta converter, 155
- multi-level
  - using flying capacitor, 104–106
- pulse-width modulated, 76
- switch implementation, 23, 84–88
- switch stress, 142
  - See also* direct converter, indirect converter
- deadbeat, 432
- delay angle, *see* SCR
- describing function, 264
- device circuit symbols, 2
- dielectric relaxation
  - in a metal, 462
  - in a semiconductor, 462
- differential mode, 783
  - (*see also* EMI)
- diffusion length, 475
- diode, 3, 439–442, 494–511
  - analysis of, 472–478
  - bipolar, 440, 494–507
    - avalanche breakdown, 497
    - conductivity modulation, 495
    - fast-recovery, 441, 542
    - forward bias, 499
    - forward drop, 440, 441
    - forward recovery, 440, 504
    - high-current effects, 503
    - leakage current, 440, 495–497
    - pin diode, 498–507
    - reverse recovery, 441, 495, 506
    - reverse recovery time, 441
    - slow recovery, 441
    - switching dynamics, 504
    - temperature dependence, 503
  - freewheeling, 32
  - peak inverse voltage, 440
  - punch-through, 478
  - reverse leakage current, 476
  - saturation current, 476
  - Schottky, 438, 494, 507–511
    - forward drop, 440, 441
    - leakage current, 440
    - recovery characteristics, 441
    - SiC, 529
  - snappy, 441
  - soft-recovery, 441
  - voltage rating, 440
  - Zener
    - as clamp, 139
- direct converter, 82–88
  - ripple-frequency model, 96
  - switch stress, 103
  - with bilateral power, 86
- discrete-time, *see* sampled-data
- displacement factor, *see* power factor
- distortion
  - measures and effects of, 38–44
- distortion factor, *see* power factor
- DLC, *see* electric double-layer
- Dowell's equation, 660
- down converter, *see* buck converter
- dual converter, 72
- duty ratio, 19, 77, 88
- dynamic phasor, 351, 373
- eddy current, 438
- Edison, Thomas, 27, 49
- eigenvalue, 31, 387
- Einstein relation, 501
- electric double-layer, *see* capacitor

## 796 Index

- electromagnetic interference, *see* EMI, 771
- electron
  - mobile, 462
- EMI, 570, 599, 725, 747, 771–789
  - LC* filter, 773–777
    - damping, 774–777
    - negative damping, 775
    - output impedance, 776
  - circuit layout, 788–789
    - magnetic coupling, 789
    - parasitic capacitance, 789
  - common- and differential-mode filter, 785
  - common-mode, 783–784
    - choke, 785
    - filter, 785
    - model, 785
  - conducted, 771–773
  - converter–filter interactions, 777–780
    - negative resistance, 778
    - stability, 778
  - differential-mode, 783–784
    - filter, 785
    - model, 785
  - element parasitics, 787–788
  - filter design, 773–780
    - input filter
      - control dynamics, 779
    - LISN, 772
    - measurement, 771–773
    - multi-stage filter, 777
    - specifications, 773
  - equivalent series resistance, *see* ESR
    - ESR, 110, 350
  - FHA, *see* fundamental harmonic approximation
  - filter, 16
    - effectiveness, 79
    - for direct converter, 98
    - higher-order, 81
    - low-pass, 16, 76–78
    - second-order, 16
      - See also* EMI
  - firing angle, *see* SCR
  - flux linkage  $\lambda$ , 547
  - flyback converter, 136
    - in dc/ac application, 195
  - flyforward converter, 141
  - flying capacitor, 104–106, 190–192
  - forward converter, 136
  - isolated single-ended, 136–144
  - forward Euler method, 359
  - Fourier series, 28, 43, 172–175, 314
  - fundamental harmonic approximation, 256
  - gallium nitride, *see* GaN
    - GaN, 494, 497
      - dynamic on-state resistance, 530
      - HEMT, 530
      - MOSFET, 528–530
        - See also* MOSFET
    - gate drive, 693–695, 704
      - See also* MOSFET, SCR
    - gate turn-off thyristor, *see* GTO
    - Greinacher voltage multiplier, 131
    - GTO, 4, 450, 537
      - snubber requirement, 450
      - turn-off gain, 450
      - turn-off requirements, 450
    - harmonic cancellation, 177–179
    - harmonic elimination, 175–177
    - heat sinking, 701, 753
    - heat transfer, 753
      - conduction, 753
      - convection, 753
        - film coefficient of, 755
        - flow boundary, 762
        - forced, 755
        - natural, 755
        - Reynolds number, 756, 762
    - junction temperature, 760
    - radiation, 753, 754
    - thermal interface, 758, 760
      - materials, 756
      - thermal grease, 756
    - thermal system, 758
    - through PC board, 761
    - heatsink, 701
      - finned, 701, 761
    - $h_{FE}$  (current gain), *see* BJT
    - high-level injection, 494, 499, 500, 502
      - in BJT, 511
    - homogeneous response, 31
    - hysteresis, 555
    - IGBT, 2, 4, 524–528
      - capacitances, 527
      - collector current tail, 528
      - collector cut-off current, 527
        - dynamic behavior, 527
    - equivalent circuit, 447
    - forward drop, 526
    - gate drive, 704–713
      - requirements, 706
    - off state, 527
    - physical structure, 524
    - switching dynamics, 448
    - indirect converter, 82, 89–91, 95
      - conversion ratio, 89
      - ripple-frequency model, 97
      - switch implementation, 90
      - variations of, 91
    - inductance
      - calculation of, 547–549, 551
      - definition of, 547
      - flux linkage  $\lambda$ , 546
      - second-order effects, 552–553
    - inductance matrix, *see* transformer
    - inductor, 455, 546–555
      - ac
        - loss minimization, 630–631
        - power rating, 624–625
      - core area product ( $A_C W_A$ ), 625
      - core factor, 615, 617–618
      - core selection example, 617
      - design example, 636–638
      - energy storage, 553–555
      - energy storage limit, 621–623
      - filter, 618
      - filter inductor, 613
        - design of, 563
      - loss model, 564
      - losses in, 439
      - mean length of turn, 613
      - packing factor, 558
      - shield winding, 598–600
        - cutoff frequency, 600
        - design of, 600
      - toroidal, 548
      - winding resistance (dc), 614
      - with air gap, 551, 613
      - with distributed gap, 551
    - insulated-gate bipolar transistor, *see* IGBT
    - inverter
      - current-source inverter, 167, 171
        - $\delta$  control of, 171
        - $\theta$  control of, 171
        - average power calculation, 171
        - direction of power, 171
        - need for bidirectional switches, 172
      - definition, 14

- multi-level, 237–240
- neutral-point clamped, 238–240
  - See also* NPC
- phase-controlled, 57
- power factor, 168
- three-phase, 221–228
  - PWM of, 227–228
  - switching states, 224–227
- voltage-source
  - non-unity-power-factor load, 169
- voltage-source inverter
  - non-unity-power-factor load, 169
- $k_\theta$ , *see* displacement factor
- $k_d$ , *see* distortion factor
- Kelvin connection, 708, 710, 713
- $k_p$ , *see* power factor
- $L_a$ , *see* ambipolar diffusion length
- leakage inductance, 155
- level shifting, 709
- light dimmer, 457
- line-impedance stabilization network (LISN), *see* EMI
- linear time-invariant (LTI), 322, 357
- linearity, 356
- LISN, *see* EMI
- litz wire, 560
- Litzendraht, 560
- load regulation, *see* rectifier
- local  $\omega_s$ -component, 316
- local average, 315, 323
- local averaging, 346
- local fundamental, 350
- low-level injection, 478, 494
- magnetic circuit, 550, 583
  - transference, 598
- magnetic circuit model
  - for component design, 605
  - stored energy, 605
  - synthesizing from electric circuit model, 603
  - transference, 600
- magnetic components, 455
  - core geometries, 456
  - losses in, 566
- magnetic diffusion, 643–655
  - diffusion equation, 643–644
    - one-dimensional, 644–646
  - diffusion wave, 646
  - skin depth, 645
- magnetic materials, 456, 575–576
  - ferrites, 456, 561, 576
  - ferrous alloys, 456, 561
- magnetics, 545
  - ac, 624–634
  - ampere-turns, 549
  - core geometries, 615
  - design of, 612–638
  - electric circuit analog, 549
    - example, 550
    - permeance, 549
    - reluctance, 549
  - losses in, 456, 557–684
    - modeling, 597
    - scaling with volume, 558
- materials
  - performance factor, 634–636
- packing factor  $k_u$ , 613
- residual flux, 555–557
- RM core, 558
  - data, 615
- saturation, 556
- thermal constraints, 618–621
- winding loss, *see* winding loss
- window utilization factor  $k_u$ , 613
- magnetizing current
  - resetting, 138
- magnetomotive force, *see* MMF
- matrix converter, 305
- Maxwell's equations, 546, 546
- McMurray, William, 302
- mean length of turn, *see* inductor
- metal-oxide field-effect transistor, *see* MOSFET
- metal-oxide varistor
  - as clamp, 139
- method of assumed states, 46
- MMF, 550
- MOSFET, 2, 4, 483–524
  - body diode, 446
  - calculating fall time, 707
  - capacitances, 485
  - carrier saturation velocity, 519
  - channel, 483
    - inversion of, 483
    - resistance, 446
  - characteristics, 484
  - datasheet, 538–541
  - DMOS, 517
  - drain resistance, 446
  - dynamic behavior, 521
  - enhancement mode, 484
- extended drain, 517
- GaN, 528–530
- gate capacitance
  - charge vs. voltage, 707
- gate drive, 446, 704–713
  - common-mode transient immunity, 710
  - dead-time, 709
  - EMI problem, 713
  - level shifting, 709
  - loss, 708
  - requirements, 706
  - shoot-through, 708
- lateral, 483
- linear region, 484
- Miller effect, 705
- on-state resistance, 519
- parallel operation, 711
  - oscillation in, 711
- parasitic transistor, 446
- physical structure, 445
- $R_{DS(on)}$ , 446, 521
- regions of operation, 442
- safe operating area, 486, 487
- saturation region, 485
- SiC, 529
  - common-mode choke, 713
  - Kelvin connection, 708, 710, 713
- source–body short, 446
- specific on-state resistance, 519
- superjunction, 523–524
- switching waveforms
  - with clamped inductive load, 446
- threshold voltage, 445, 483, 486, 706
  - temperature dependence, 711
- to replace diode, 122
- transconductance, 485
- trench, 520
- UMOS, 520
  - $v-i$  characteristics, 442
- multi-level converter, 190
  - diode-clamped, 191
- mutual inductance
  - coupling coefficient, 583
- natural frequencies, 31, 336, 387
- natural response, 389
- neutral-point clamped inverter, *see* NPC
- $n_i$ , 463
- nomenclature, 7
- nominal operation, 313

**798      Index**

- NPC
  - single-phase, 192
  - three phase, 238–240
- Nyquist criterion, 338
- Nyquist plot, 406
- Nyquist stability, 406–407
- packing factor, 558
- parasitics
  - modeling of, 596
- Park transform, 234
- particular response, 31
- peak inverse voltage, *see* diode
- periodic operation, 314
  - deviations from, 315
- periodic steady state, 15, 33
- permeability
  - definition of, 546
  - normalized to free space  $\mu_0$ , 546
- permeance, 549
- PFC, 197–201
  - control of, 201
  - storage capacitor sizing, 200
- phase-controlled converter, 16, 57–71
  - as battery charger, 66
  - commutation failure, 67–71
  - control characteristic, 59
    - linearizing, 59
  - in dc-link converter, 291
  - inversion limits, 67
  - inversion region, 62
  - magnet discharge example, 62, 72
    - with commutating reactance, 70
  - margin angle, 69, 71
  - power factor, 63
  - quadrants of operation, 61
  - reactance factor, 70
  - regulation curves, 65
  - single-phase, 58
  - three-phase bridge, 215
    - with commutating reactance, 64
      - See also* controlled rectifier
  - phasor, 233
  - PIV, *see* peak inverse voltage
  - polyphase sources, 207–213
    - balanced, 207
    - creating rotating fields, 208
    - phasor diagram, 208
    - phasor representation, 207
    - three-phase, 209
      - $\Delta$ -connected, 210
      - balanced load, 211
      - calculating power, 212
  - cancellation of triple- $n$  harmonics, 212
  - line voltages, 210–211
  - neutral-point connection, 210
  - phase-shifting connections, 211
  - Y-connected, 210
  - power
    - in electrical networks, 27
  - power factor, 39–44
    - angle, 40
    - apparent power, 38
    - compensation of, 41
    - displacement factor, 41
    - distortion factor, 41
    - in polyphase rectifier, 217
    - of ac controller, 39
    - of distorted waveforms, 41
    - of single-phase bridge, 46
    - of sinusoidal waveforms, 40
    - reactive power, 40
  - power factor correction, *see* PFC
  - proximity effect, 438, 560
  - proximity loss, 665
  - pulse-width modulation, *see* PWM, 179–187
  - punch-through, 478
  - push–pull converter, 148
  - push–pull inverter, 278
  - PWM, 76, 84, 172
    - modulation index, 180, 185
    - naturally sampled, 184
    - sine–triangle intercept, 184
    - See also* dc/ac converter
  - $Q$ , *see* quality factor
  - quality factor, 253, 352
  - reactive power, 40, 187, 289, 293, 624
  - rectifier, 14
    - 12-pulse, 213
    - 6-pulse, 213
    - commutating inductance, 35
    - current commutation, 35
      - equivalent circuit, 36
    - load regulation, 31
  - PFC, 197–201
  - polyphase, 213–221
    - 12-pulse, 215
    - 6-pulse, 217
    - commutation in, 216–221
    - commutation modes, 217–221
    - full-wave bridge, 213
    - power factor, 217
  - single-phase, 27–56
    - bridge circuit, 44, 47
    - discontinuous conduction, 31
    - half-wave, 29
    - load regulation, 47
    - with capacitive filter, 34
    - with center-tapped source, 46
    - with freewheeling diode, 32
    - with inductive load, 30
    - with resistive load, 29
  - switched-mode, 197
    - synchronous, 87
  - reluctance, 549
  - residual-flux density, 555
  - resonant converter, 17, 249–283
    - analysis, 256–260
    - control
      - adaptive-power tracking, 280
      - burst-mode, 283
      - drain modulation, 280
      - envelope tracking, 280
      - out-phasing, 280–283
      - switching frequency, 267
    - dc/dc, 264–271
      - design, 267–268
      - rectifier analysis, 264–266
      - state-space model, 370
    - modeling, 266–268
    - radio-frequency, 271–283
      - class D, 272–274
      - class E, 274–278
      - dc-voltage control, 280
      - multi-switch, 278–280
      - output control, 280–283
      - push–pull, 278–280
    - series-resonant, 256
    - design, 259
    - element values, 263
    - output control, 257–259
  - soft switching, 260–264
    - above-resonance operation, 261
    - below-resonance operation, 261
    - circuit model, 261
    - switch stress, 249
  - resonant dc/dc converter
    - state trajectories, 359
  - resonant-transition converter, 741–747
  - Reynolds number, 756, 762
  - ripple instability, 401
  - ripple ratio, 99
  - root locus, 337, 344, 382

- safe operating area, *see* SOA
- sampled data, 365
- saturation, 556
- saturation-flux density, 555
- SCC, *see* switched-capacitor converter
- SCL, *see* space-charge layer
- SCR, 2, 4, 448, 494, 530–537
  - angle of retard, 59
  - asymmetrical SCR (ASCR), 449
  - characteristics, 57
  - circuit commutated turn-off time, 448, 536
  - delay angle, 59
  - $di/dt$  limit, 534
  - $dv/dt$  limit, 534, 536
  - firing angle, 59
  - forced commutation, 695–697
    - limitations of, 696
  - forward breakdown voltage, 448
  - gate drive, 694, 704, 716–718
    - isolation, 716
    - parameters, 717
    - pedestal and porch, 717
    - rate effects, 718
    - requirements, 717
  - holding current, 534
  - inverter-grade, 449
  - latching current, 534
  - margin angle, 69
  - opto-SCR, 535
  - rectifier-grade, 449
  - regenerative turn-on, 532
  - reverse recovery, 448
  - trigger mechanisms, 448
  - two-transistor model, 532
- second-order systems, 250–254
  - frequency-domain response, 252–254
  - quality factor, 254–256
  - time-domain response, 250–252
- semiconductor
  - acceptor impurities, 463
  - bandgap, 462
  - carrier concentration, 464
    - at SCL edge, 473
    - calculation of, 464
    - excess notation, 474
    - in short diode, 477
    - in thermal equilibrium, 463
    - intrinsic, 463
    - thermal generation of, 464
  - carrier recombination, 462
    - rate of, 462
  - charge carriers, 461
- charge neutrality, 464
- charge transport, 465
  - by diffusion, 465
  - by drift, 465
- conductivity of, 466
- current densities
  - calculation of, 466
- diffusion constants, 466
- donor impurities, 463
- doping, 463
- extrinsic, 461, 463
- hole, 462
- intrinsic, 461
- majority carrier, 439
- majority-carrier device, 439
- materials
  - parameters of, 466
- minority carrier, 439
- minority-carrier device, 439
- p–n junction
  - abrupt SCL model, 468
  - built-in potential, 470
  - in thermal equilibrium, 468
  - space charge layer, 468
  - space-charge layer, 472
  - physics of, 461
- semiconductor
  - GaN, 440
  - SiC, 440
- SEPIC converter, 94–95, 154
- series-resonant converter
  - switching-frequency dynamics, 351
- shaded-pole motor, 598
- shield winding, 598–600
- SiC, 497, 528
  - MOSFET, 529
  - Schottky diode, 529
- silicon carbide, *see* SiC
- silicon controlled rectifier, *see* SCR
- silicone grease, *see* thermal grease
- skin depth, 560, 645
- skin effect, 438, 560
- sliding mode, 424
- snubber, 50, 697
  - alternative placements, 735
  - basic operation of, 697
  - combined turn-on/off, 733–734
    - transient voltage, 733
  - dissipation, 736
    - in combined circuit, 737
    - in turn-off circuit, 736
    - in turn-on circuit, 736
  - net circuit increase, 737
- EMI reduction, 747
- turn-off, 725–729
  - basic circuit, 727
  - loss, 727
  - RCD circuit, 729
  - turn-on, 730–733
    - basic circuit, 731
    - dissipation, 730
    - RLD circuit, 732–733
- SOA, 486, 540, 724, 726, 764–767
- soft switching, 697–699, 725, 739–747
  - EMI reduction, 747
  - implementation, 740
  - limitations, 747
- solid-state transformer, 290, 302
- space vector, 229–234
- space-charge layer, 468, 472
  - calculation of width, 470, 472
  - incremental capacitance of, 473
- space-vector modulation, 229, 234–237
- SST, *see* solid-state transformer
- start-up problem, 556
- state variables, 355, 361
  - continuity property, 359
  - flux and charge as, 363
  - state evolution, 356
  - state plane, 360
  - state property, 358–361
  - state trajectories, 359, 370
- state-space averaging, *see* control
- state-space models, 323
  - for electrical circuits, 361–363
  - numerical solution of, 359
- state-transition matrix, 372
- Steinmetz equation, 679
  - improved, 680
- switch stress, 103, 108, 142, 249
- switch-stress factor, 103
- switch-stress parameter, 103
- switched-capacitor converter, 116–131
  - characteristics, 116
  - charge multipliers, 128
  - charge transfer
    - calculation of, 126
  - Cockcroft–Walton voltage multiplier, 131
  - fast-switching limit, 119, 129
  - parasitic resistance, 120
  - Thévenin equivalent, 120
  - voltage ratio, 120, 121
- Greinacher voltage multiplier, 131
- hybrid converter, 132
- ladder network, 124

800      **Index**

- charge calculations, 127
- slow-switching limit, 118, 127
- Thévenin equivalent, 119
- switch implementation, 121
- two-state, 118
- switching function, 327, 348
  - generation of, 328
  - modulating signal, 329
- switching loss, 438, 725, 726
- switching surface, 423
- synchronous rectifier, 87, 122
- Tellegen's theorem, 128
- THD, 38, 42
  - calculation of, 43, 183
- thermal grease, 756
- thermal impedance, 761
- thermal interface, 758, 760
  - convective, 761
  - silicone pad, 760
- thermal models, 700, 753
  - circuit analog, 754, 757
  - static, 754
  - thermal power, 754
  - thermal resistance, 754, 755
  - thermal resistivity
    - of sheet, 756
  - transient, 762
    - design example, 764
    - distributed, 763
    - dynamic behavior, 764
  - heat capacity, 762
  - multi-lump, 763
  - thermal impedance, 763
- thermal resistivity, 756
  - of materials, 756
  - units of, 756
- three-phase systems, 229–234
  - $(\alpha, \beta, \gamma)$  coordinates, 230–234
    - common-mode component, 230
  - Clarke transform, 231–234
  - $d-q-0$  coordinates, 234
  - Park transform, 234
  - space vectors, 229–234
- threshold voltage, *see* MOSFET
- thyristor, 2, 4, 57, 530–538
  - family members, 448
  - See also* SCR, TRIAC, GTO
- time invariance, 356
- topological duality, 603
- total harmonic distortion, *see* THD
- $t_q$ , *see* circuit commutated turn-off time
- transfer function, 335, 402
  - hidden poles, 336
- transference, 598, 600
- transform domain, 386
- transformer, 5, 455, 566
  - $\pi$ -model, 586
  - cantilever model, 586
    - extended, 589–591, 594
    - parameter extraction, 590
    - shortcoming, 591
  - current, 572–574
    - burden, 572
  - decoupled model, 594
  - design example, 627–629
  - dot convention, 5, 567, 575
  - electric circuit models, 602, 603
  - energy storage, 572
  - extracting parameters, 587–588
  - flux resetting, 138
  - flyback, 154
  - foil windings, 570
  - ideal, 5, 566–567
  - inductance matrix, 582
    - example, 583
    - reciprocity of, 582
    - symmetry of, 582
  - inter-winding leakage, 587
  - L-model, 586
  - leakage inductance, 6, 569–570, 584–588
  - loss minimization, 631–634
  - magnetic circuit
    - electrical coupling of, 601
  - magnetizing current, 5
  - magnetizing inductance, 5, 567–569
  - models, 566–575, 582–607
    - multi-winding, 588–597
    - negative inductance in, 586
    - of two-port, 584–586
    - with dependent source, 594
  - mutual inductance, 583
  - parameter extraction, 571–572
  - potential, 572
  - power rating, 625–629
  - schematic representation, 6
  - shield winding, 570
  - T-model, 585
  - terminal equations, 571–572
  - three-winding, 574
  - winding build-up, 570
  - tri-state inverter, 168, 170, 175
  - TRIAC, 58, 537
  - commutating  $dv/dt$ , 451
  - gate current requirements, 450
  - quadrants of operation, 451
  - triode ac switch, *see* TRIAC
  - triple- $n$  harmonics, 175
  - uninterruptible power supply, *see* UPS
  - up converter, *see* boost converter
  - up/down converter, *see* buck/boost converter
  - UPS, 22
  - voltage-source inverter, 167
  - $V_T$ , *see* threshold voltage
  - waveform properties, 172–175
    - even/odd decomposition, 173
    - half-wave repeating, 173
    - half-wave symmetric, 173, 175
    - orthogonality, 174
    - symmetry, 173–175
      - See also* Fourier series
  - Westinghouse, George, 27, 49
  - Wiedemann–Franz law, 756
  - winding loss, 558–561, 624, 655–675
    - calculation
      - examples, 657
      - using boundary conditions, 656–658
    - calculation basics, 655–656
    - Dowell's equation, 660
    - electrical representation, 671–675
    - in multilayer winding, 658–664
      - effect of skin depth, 663
    - interleaving, 668
    - mutual resistancace, 672
    - porosity factor, 664
    - proximity effects, 665
    - resistance factor, 661, 666
    - self-resistance, 672
    - wire size, 558
      - with non-sinusoidal current, 670–671
    - winding models, 664–669
    - window utilization factor, 558
  - $Z_\theta$ , *see* transient thermal impedance
  - ZCS, 697, 739–747
  - zero-current switching, *see* ZCS
  - zero-voltage switching, *see* ZVS
  - Zeta converter, 155
  - ZVS, 697, 739–747